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AO3414 N-Channel Enhancement MOSFET

SOT-23-3 Plastic-Encapsulate MOSFETS

产品规格书

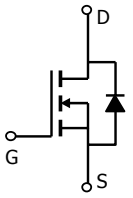
承认书

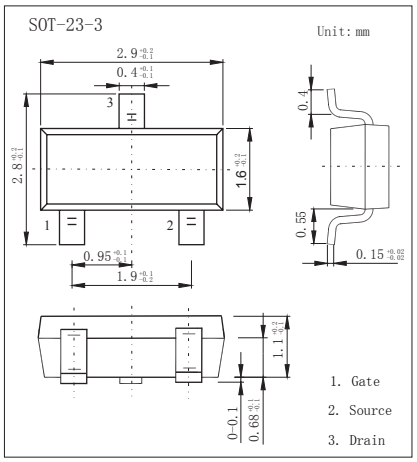
客户确认：				公司签章：
部门	工程部	品保部	采购部	
签名				
日期				

AO3414 N-Channel Enhancement MOSFET

■ Features

- $V_{DS\ (V)}$ = 20V
- I_D = 4.2A (V_{GS}=4.5V)
- $R_{DS(ON)}$ < 50mΩ (V_{GS} = 4.5V)
- $R_{DS(ON)}$ < 63mΩ (V_{GS} = 2.5V)
- $R_{DS(ON)}$ < 87mΩ (V_{GS} = 1.8V)





■ Absolute Maximum Ratings Ta = 25℃

Parameter	Symbol	Rating	Unit
Drain-Source Voltage	V_{DS}	20	V
Gate-Source Voltage	V_{GS}	±8	V
Continuous Drain T_A=25℃	I_D	4.2	A
Current *1 T_A=70℃		3.2	
Pulsed Drain Current *2	I_{DM}	15	
Power Dissipation *1 T_A=25℃	P_D	1.4	W
T_A=70℃		0.9	
Themal Resistance.Junction-to-Ambient *1	R_{thJA}	125	℃/W
Themal Resistance.Junction-to-Case	R_{thJC}	80	℃/W
Junction and Storage Temperature Range	T_J, T_{STG}	-55 to 150	℃

*1The value of R èJA is measured with the device mounted on 1in ^{2} FR-4 board with 2oz.

Copper, in a still air environment with T_A =25℃

■ Electrical Characteristics Ta = 25℃

Parameter	Symbol	Testconditions	Min	Typ	Max	Unit
Drain-Source Breakdown Voltage	V_{DSS}	I_D=250uA,V_{GS}=0V	20			V
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS}=16V, V_{GS}=0V			1	μA
		V_{DS}=16V, V_{GS}=0V ,T_J=55℃			5	
Gate-Body leakage current	I_{GSS}	V_{DS}=0V, V_{GS}=±8V			±100	nA
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS}=V_{GS} I_D=250ì A	0.4	0.6	1	V
Static Drain-Source On-Resistance	$R_{DS(ON)}$	V_{GS}=4.5V, I_D=4.2A		41	50	mΩ
		V_{GS}=4.5V, I_D=4.2A T_J=125℃		58	70	
		V_{GS}=2.5V, I_D=3.7A		52	63	
		V_{GS}=1.8V, I_D=3.2A		67	87	
On state drain current	$I_{D(ON)}$	V_{GS}=4.5V, V_{DS}=5V	15			A
Forward Transconductance	g_{FS}	V_{DS}=5V, I_D=4.2A		11		S
Input Capacitance	C_{iss}	V_{GS}=0V, V_{DS}=-10V, f=1MHz		436		pF
Output Capacitance	C_{oss}			66		pF
Reverse Transfer Capacitance	C_{rss}			44		pF
Gate resistance	R_g	V_{GS}=0V, V_{DS}=0V, f=1MHz		3		Ω
Total Gate Charge	Q_g	V_{GS}=4.5V, V_{DS}= =10V, I_D=4.2A		6.2		nC
Gate Source Charge	Q_{gs}			1.6		nC
Gate Drain Charge	Q_{gd}			0.5		nC
Turn-On DelayTime	$t_{D(on)}$	V_{GS}=4.5V, V_{DS}=10V, R_L=2.7Ω,R_{GEN}=6Ω		5.5		ns
Turn-On Rise Time	t_r			6.3		ns
Turn-Off DelayTime	$t_{D(off)}$			40		ns
Turn-Off FallTime	t_f			12.7		ns
Body Diode Reverse Recovery Time	t_{rr}	I_F=4A, dI/dt=100A/μs		12.3		ns
Body Diode Reverse Recovery Charge	Q_{rr}	I_F=4A, dI/dt=100A/μs		3.5		nC
Maximum Body-Diode Continuous Current	I_S				2	A
Diode Forward Voltage	V_{SD}	I_S=1A,V_{GS}=0V		0.76	1	V

■ Marking

Marking	AE*

■ Typical Characterisitics

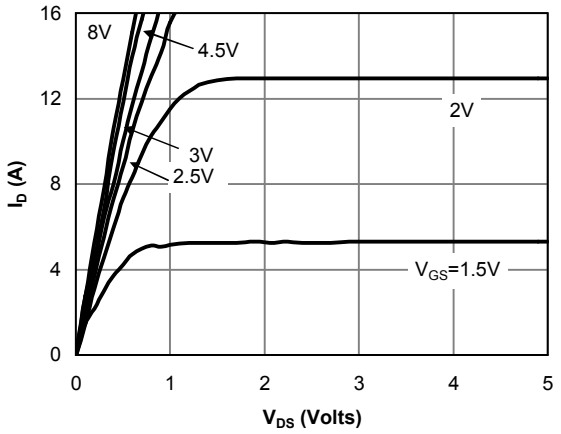


Fig 1: On-Region Characteristics

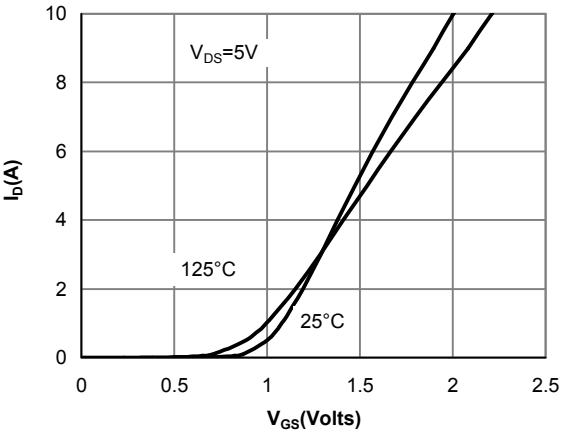


Figure 2: Transfer Characteristics

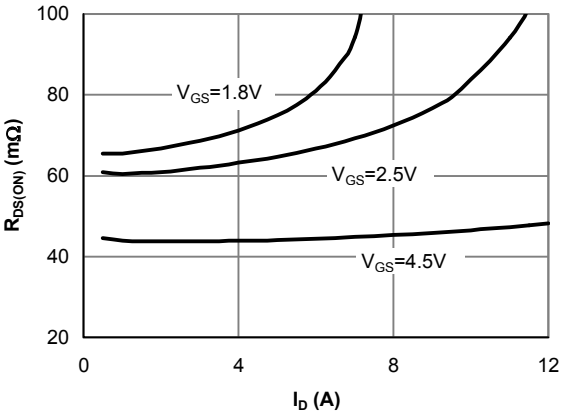


Figure 3: On-Resistance vs. Drain Current and Gate Voltage

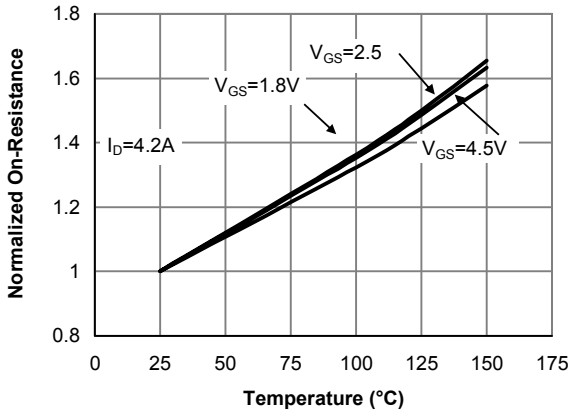


Figure 4: On-Resistance vs. Junction Temperature

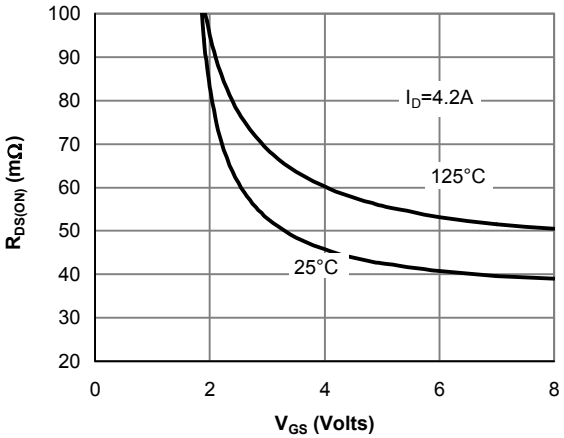


Figure 5: On-Resistance vs. Gate-Source Voltage

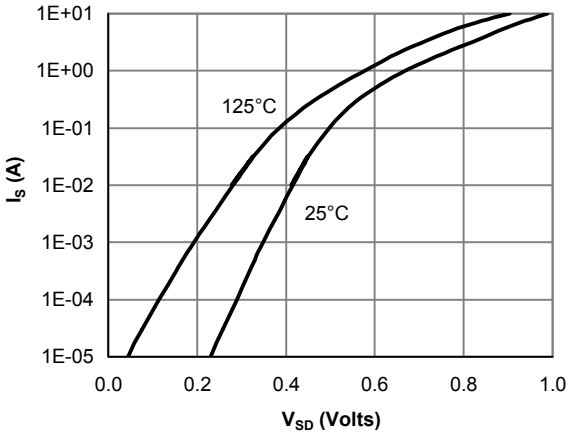


Figure 6: Body-Diode Characteristics

■ Typical Characterisitics

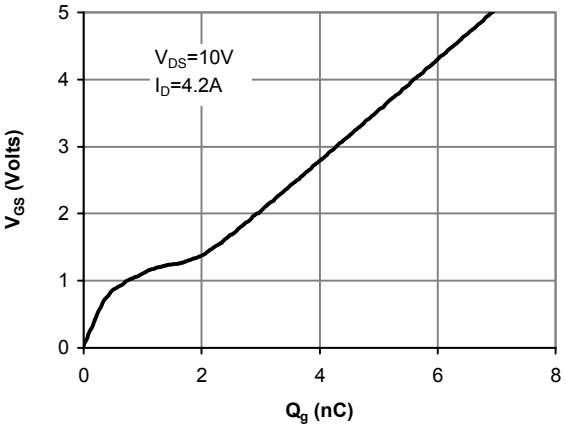


Figure 7: Gate-Charge Characteristics

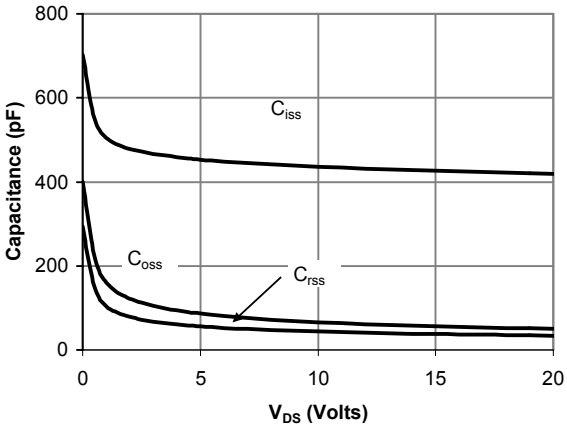


Figure 8: Capacitance Characteristics

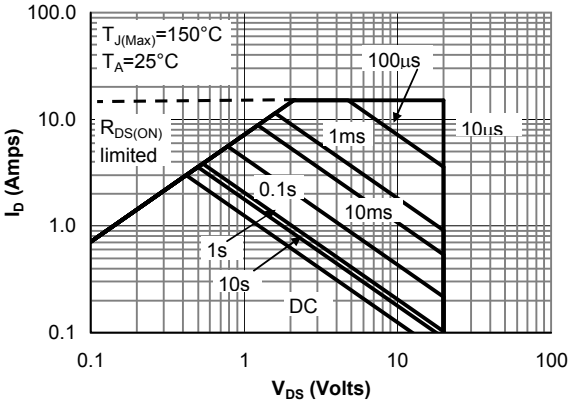


Figure 9: Maximum Forward Biased Safe Operating Area (Note E)

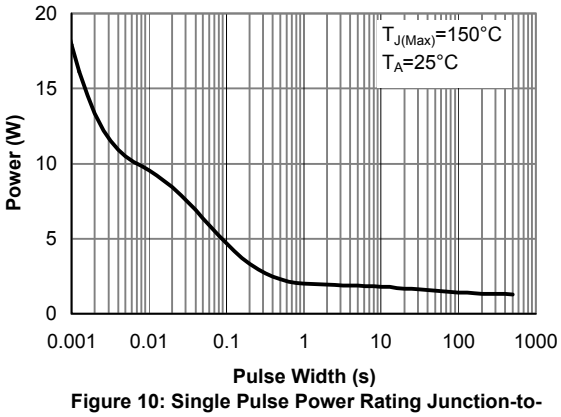


Figure 10: Single Pulse Power Rating Junction-to-Ambient (Note E)

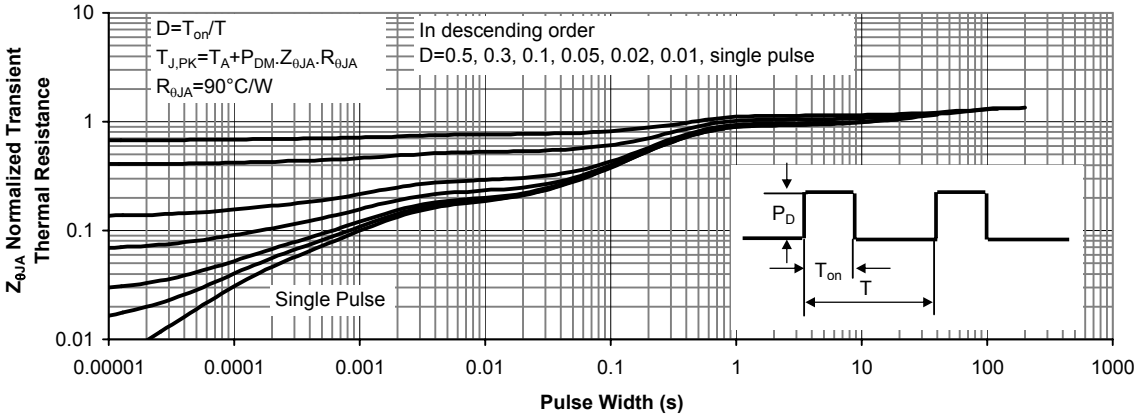


Figure 11: Normalized Maximum Transient Thermal Impedance